

# **BUK9M28-80E**

## N-channel 80 V, 28 m $\Omega$ logic level MOSFET in LFPAK33 19 September 2016

**Product data sheet** 

#### 1. **General description**

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 2. **Features and benefits**

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V<sub>GS(th)</sub> rating of greater than 0.5 V at 175 °C

#### **Applications** 3.

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

#### Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	80	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	33	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	75	W
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	23	28	mΩ
Dynamic characteristics							
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 5 V; T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	6.1	-	nC



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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D I
2	S	Source		
3	S	Source		G—UNA)
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9M28-80E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9M28-80E	92880E

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	80	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$		-	80	V
$V_{GS}$	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	10	V
		Pulsed; T <sub>j</sub> ≤ 175 °C	[1][2]	-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	75	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	33	Α
		V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	23.1	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; Fig. 3		-	131	Α

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Symbol	Parameter	Conditions		Min	Max	Unit	
T <sub>stg</sub>	storage temperature			-55	175	°C	
T <sub>j</sub>	junction temperature			-55	175	°C	
Source-drain	Source-drain diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	33	А	
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	131	Α	
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 33 A; $V_{sup} \le 80$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3][4]	-	42.2	mJ	

- 1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.
- [2] Significantly longer life times are achieved by lowering T<sub>i</sub> and or V<sub>GS</sub>
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.

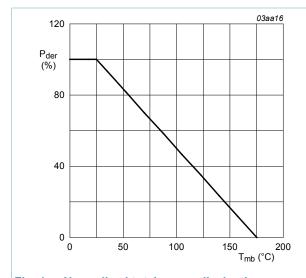
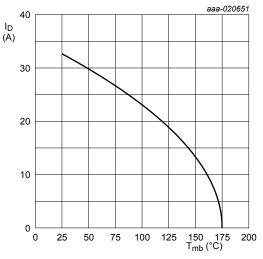


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



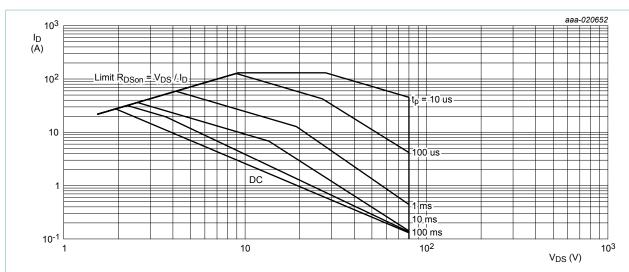
 $V_{GS} \ge 5 \text{ V}$ 

Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 33A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

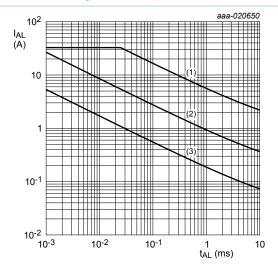
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 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1)  $T_{j \text{ (init)}}$  = 25 °C; (2)  $T_{j \text{ (init)}}$  = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

### 9. Thermal characteristics

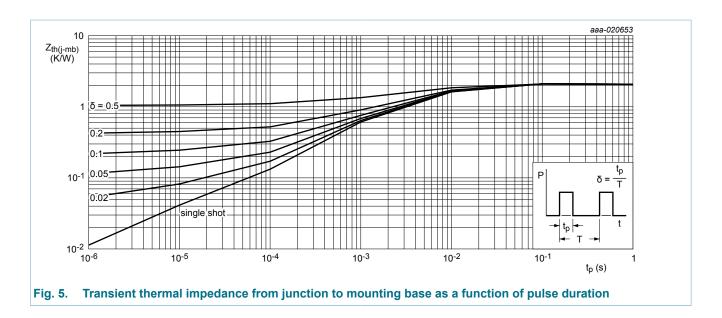
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	1.82	2	K/W

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## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 ^{\circ}C$	80	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	72	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	0.5	-	-	V
I <sub>DSS</sub> d	drain leakage current	V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μA
		V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 11$	-	23	28	mΩ
	resistance	$V_{GS}$ = 10 V; $I_{D}$ = 10 A; $T_{j}$ = 25 °C; Fig. 11	-	20	25	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 175 °C;$ Fig. 12	-	-	70	mΩ
Dynamic ch	naracteristics			1	1	
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 5 V;	-	16.7	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	4.2	-	nC

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### N-channel 80 V, 28 mΩ logic level MOSFET in LFPAK33

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$Q_{GD}$	gate-drain charge			-	6.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;		-	1711	2275	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	131	157	pF
C <sub>rss</sub>	reverse transfer capacitance			-	65	89	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 60 V; $R_{L}$ = 5 $\Omega$ ; $V_{GS}$ = 5 V;		-	10.5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$		-	17.7	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	21.8	-	ns
t <sub>f</sub>	fall time			-	14.1	-	ns
Source-dra	ain diode						
$V_{SD}$	source-drain voltage	$I_S = 10 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 ^{\circ}\text{C}$ ; Fig. 16		-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	23.8	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C		-	28.1	-	nC

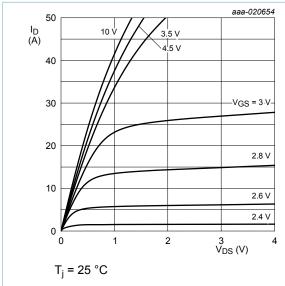


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

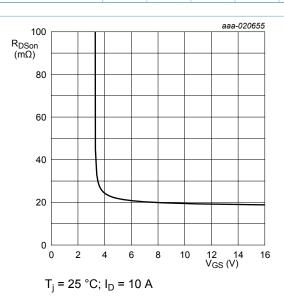


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

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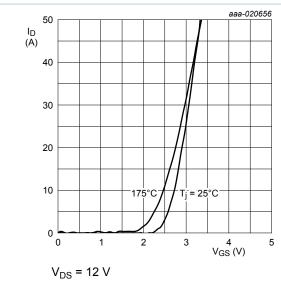


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

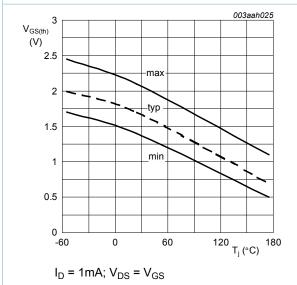
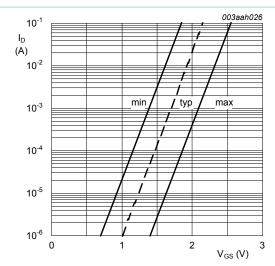


Fig. 10. Gate-source threshold voltage as a function of junction temperature



 $T_i = 25 \,^{\circ}\text{C}; \, V_{DS} = 5 \,^{\circ}\text{V}$ 

Fig. 9. Sub-threshold drain current as a function of gate-source voltage

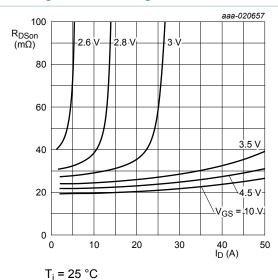


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

#### N-channel 80 V, 28 mΩ logic level MOSFET in LFPAK33

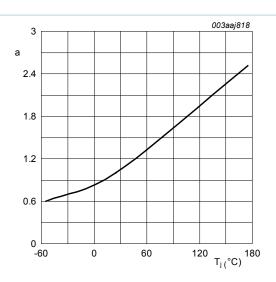


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

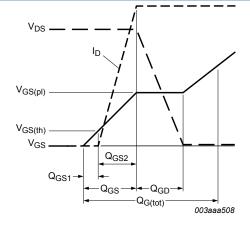


Fig. 14. Gate charge waveform definitions

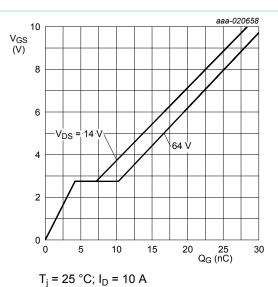
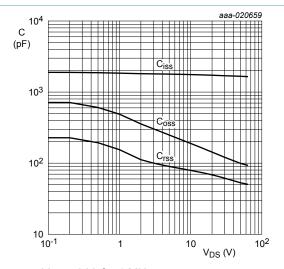


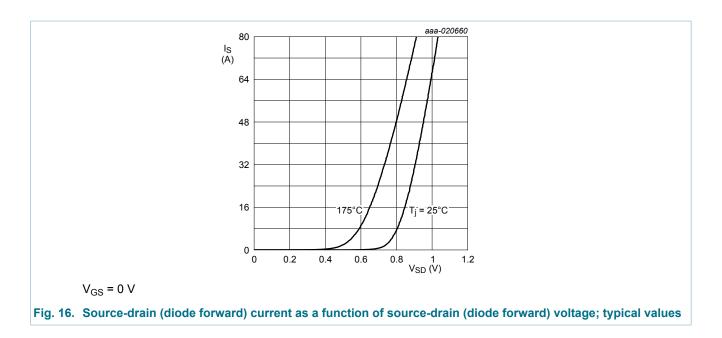
Fig. 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### N-channel 80 V, 28 m $\Omega$ logic level MOSFET in LFPAK33

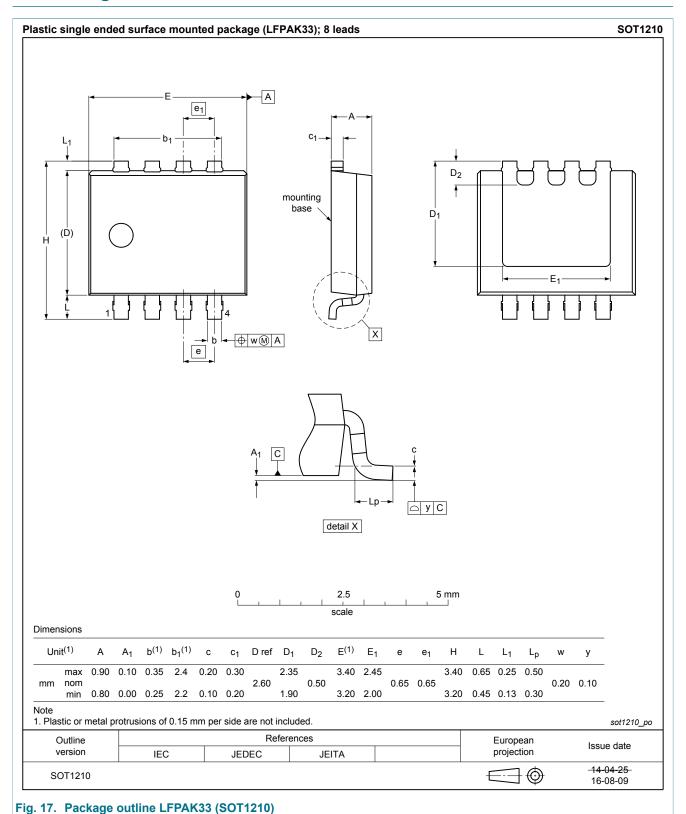


# 11. Application information

For guidance on how to use and understand this datasheet, please refer to application note AN11158 "Understanding power MOSFET datasheet parameters".

#### N-channel 80 V, 28 mΩ logic level MOSFET in LFPAK33

## 12. Package outline



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#### N-channel 80 V, 28 mΩ logic level MOSFET in LFPAK33

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